

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



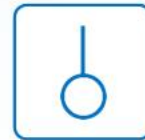
MOS



LDO



Diode



Sensor



DC-DC

Product Specification

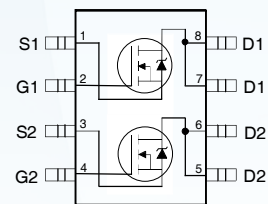
▶ Domestic	Part Number	EV-IRF7341-S2
▶ Overseas	Part Number	IRF7341
▶ Equivalent	Part Number	IRF7341

"S2" means SOP-8

EV is the abbreviation of name EVVO

Description

The EV-IRF7341-S2 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.



SOP-8

- Generation V Technology
- Ultra Low On-Resistance
- Dual N-Channel Mosfet
- Surface Mount
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free

Features

- $V_{DS} (V) = 55V$
- $I_D = 4.7A$ ($V_{GS}=10V$)
- $R_{DS(ON)} < 30m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 45m\Omega$ ($V_{GS} = 4.5V$)

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	55	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.7	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	3.8	
I_{DM}	Pulsed Drain Current ①	38	
$P_D @ T_C = 25^\circ C$	Power Dissipation	2.0	W
$P_D @ T_C = 70^\circ C$	Power Dissipation	1.3	
	Linear Derating Factor	0.016	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
V_{GSM}	Gate-to-Source Voltage Single Pulse $t_p < 10\mu s$	30	V
E_{AS}	Single Pulse Avalanche Energy ②	72	
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ⑤		62.5	°C/W

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

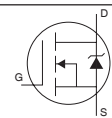
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55			V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient		0.059		V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance			30	$m\Omega$	$V_{GS} = 10V, I_D = 4.7A$ ④
				45		$V_{GS} = 4.5V, I_D = 3.8A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0			V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	7.9			S	$V_{DS} = 10V, I_D = 4.5A$
I_{DSS}	Drain-to-Source Leakage Current			2.0	μA	$V_{DS} = 55V, V_{GS} = 0V$
				25		$V_{DS} = 55V, V_{GS} = 0V, T_J = 55^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage			-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage			100		$V_{GS} = 20V$
Q_g	Total Gate Charge		24	36	nC	$I_D = 4.5A$
Q_{gs}	Gate-to-Source Charge		2.3	3.4		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge		7.0	10		$V_{GS} = 10V$, See Fig. 10 ④
$t_{d(on)}$	Turn-On Delay Time		8.3	12	ns	$V_{DD} = 28V$
t_r	Rise Time		3.2	4.8		$I_D = 1.0A$
$t_{d(off)}$	Turn-Off Delay Time		32	48		$R_G = 6.0\Omega$
t_f	Fall Time		13	20		$R_D = 16\Omega$, ④
C_{iss}	Input Capacitance		740		pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance		190			$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance		71			$f = 1.0\text{MHz}$, See Fig. 9

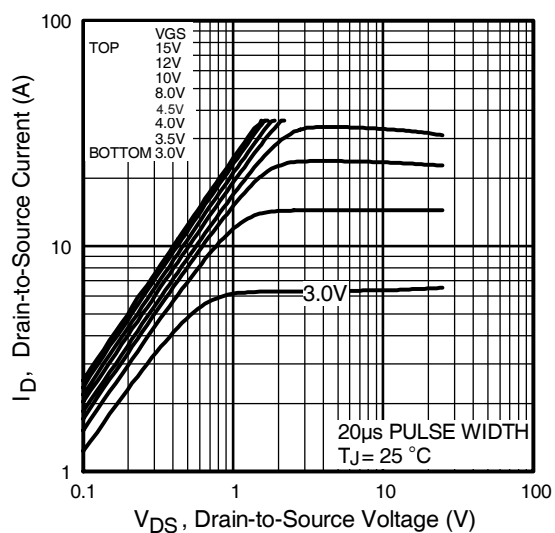
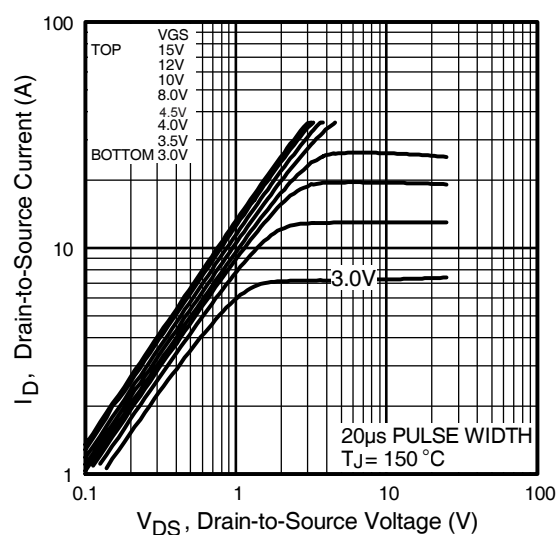
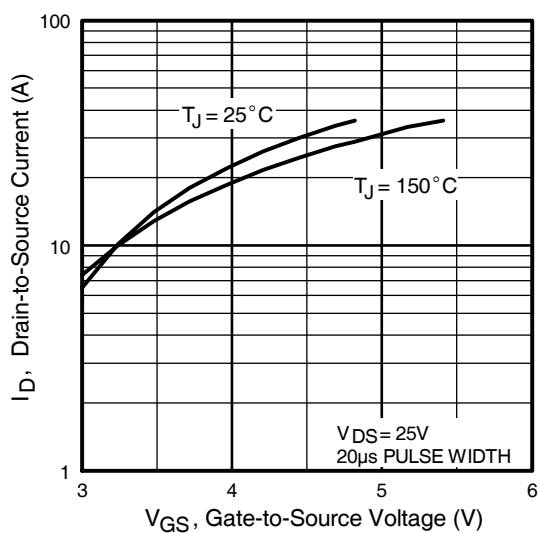
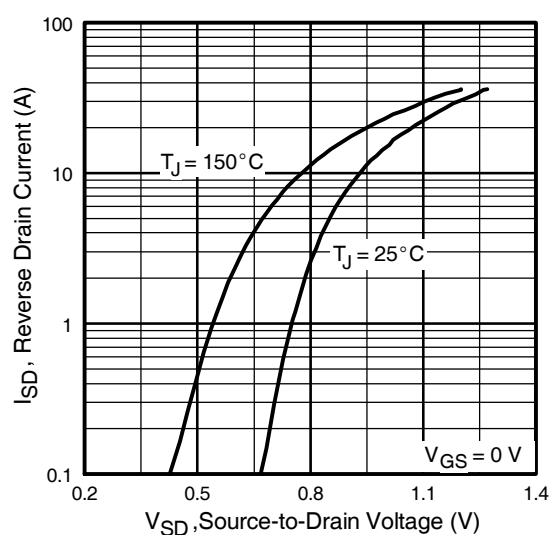
Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)			2.0	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①			38		
V_{SD}	Diode Forward Voltage			1.2	V	$T_J = 25^\circ\text{C}, I_S = 2.0A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time		60	90	ns	$T_J = 25^\circ\text{C}, I_F = 2.0A$
Q_{rr}	Reverse Recovery Charge		120	170	nC	$di/dt = -100A/\mu s$ ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 6.5\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 4.7A$. (See Figure 8)
- ③ $I_{SD} \leq 4.7A$, $di/dt \leq 220A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ When mounted on 1 inch square copper board, $t < 10\text{ sec}$



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Typical Source-Drain Diode Forward Voltage

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

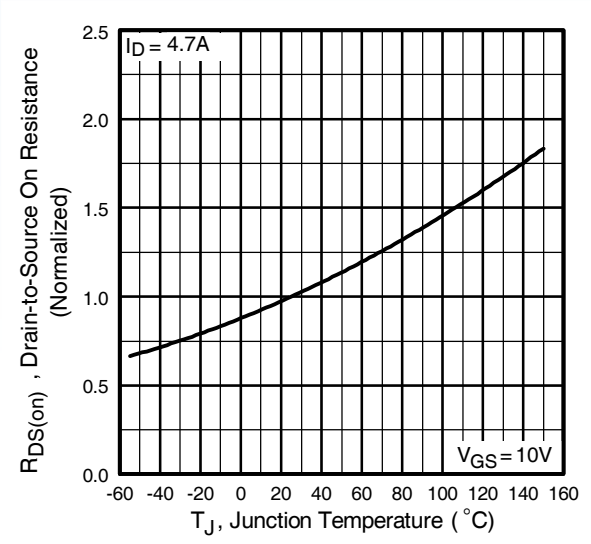


Fig 5. Normalized On-Resistance Vs. Temperature

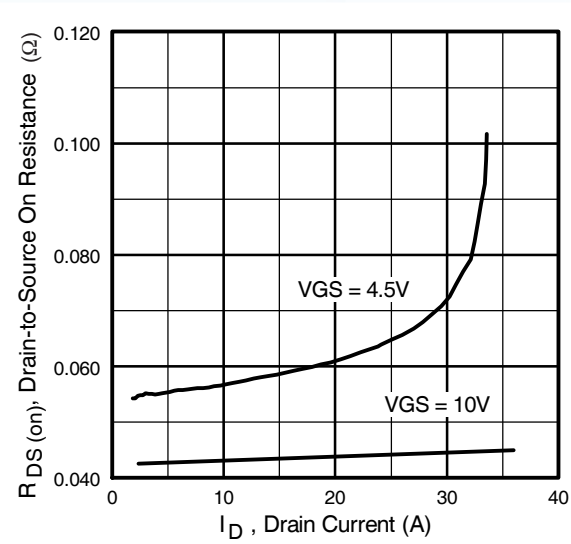


Fig 6. Typical On-Resistance Vs. Drain Current

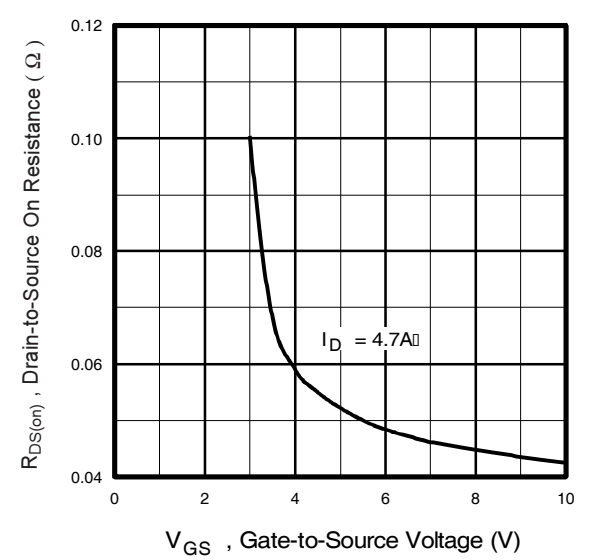


Fig 7. Typical On-Resistance Vs. Gate Voltage

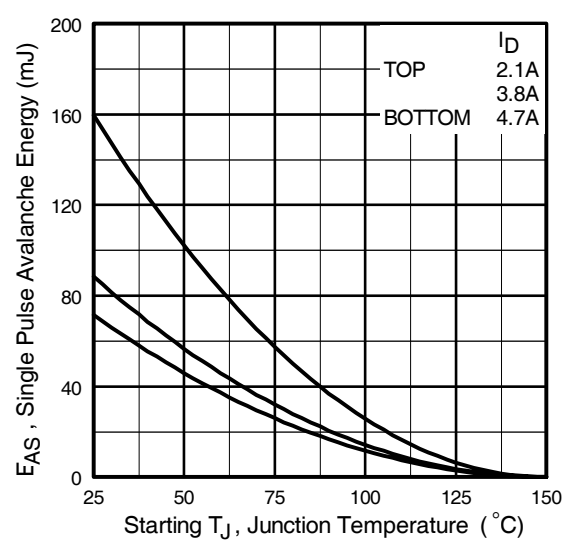


Fig 8. Maximum Avalanche Energy Vs. Drain Current

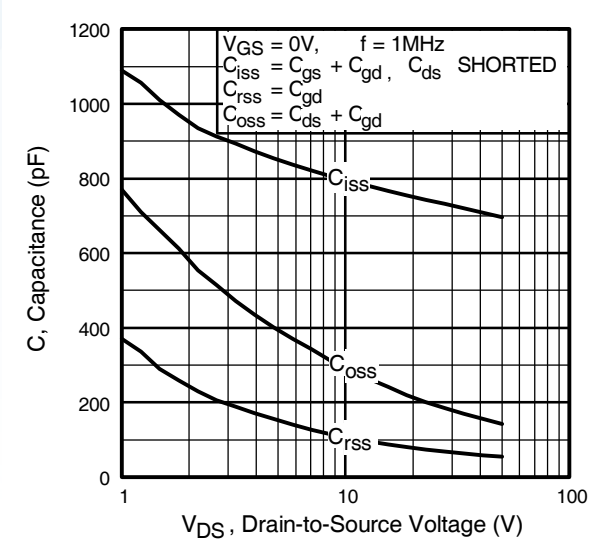


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

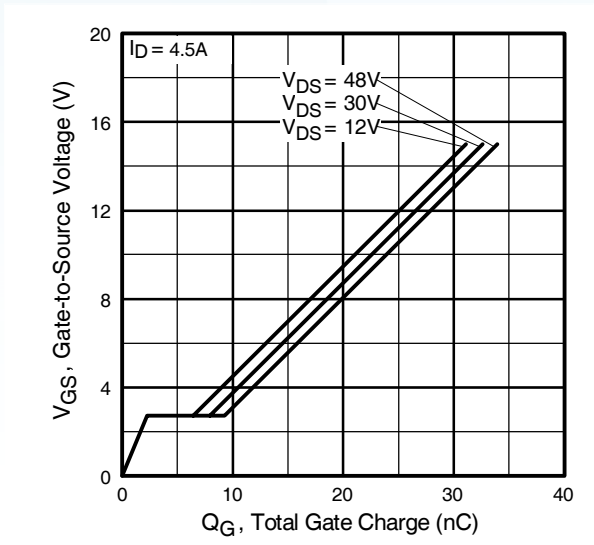


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

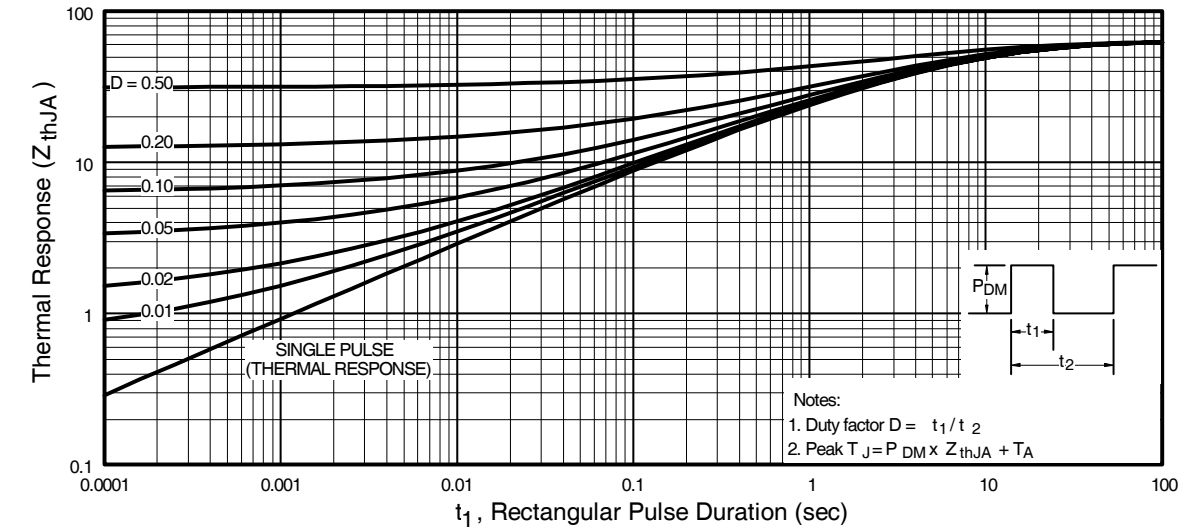
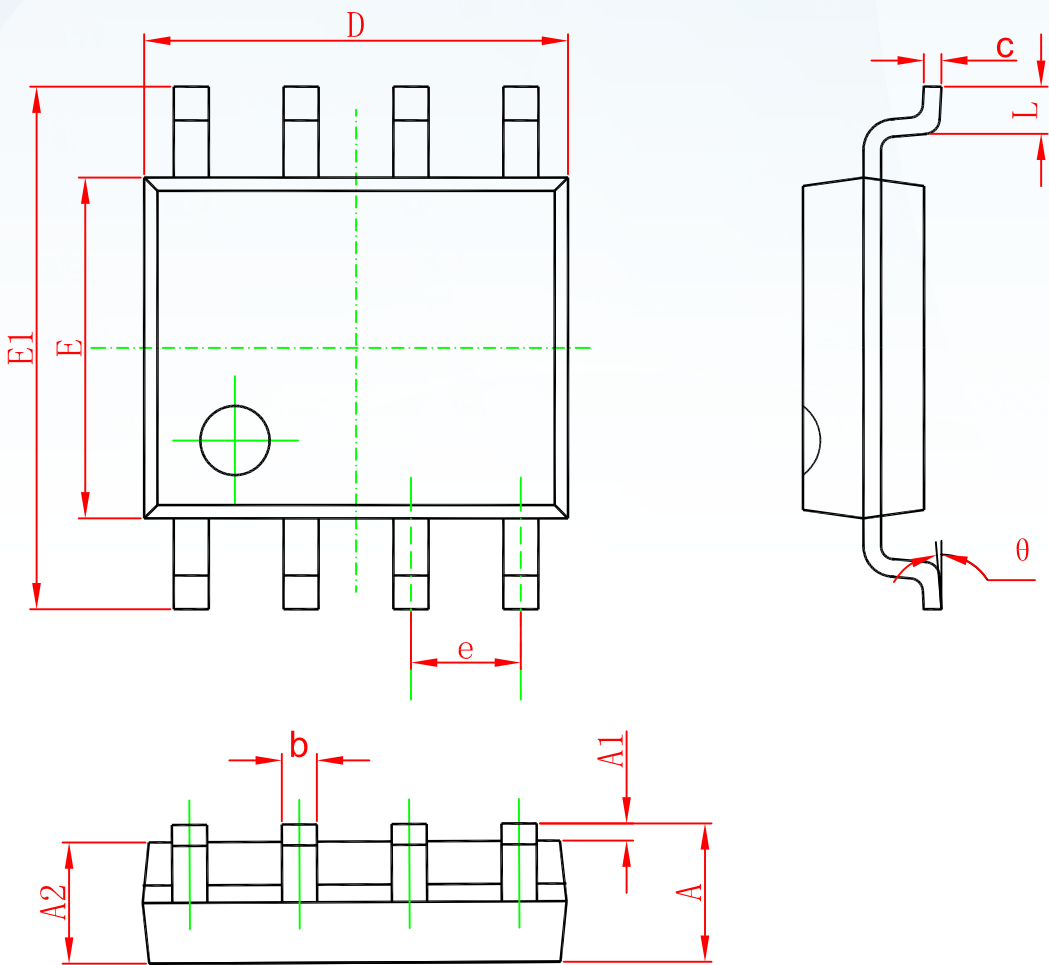


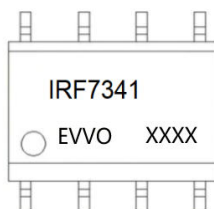
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
EV-IRF7341-S2	SOP-8	3000	Tape and reel

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